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A method and system for providing a sinker on a semiconductor device is disclosed. The method and system comprises providing a substrate region and providing a buried layer and an epitaxial (EPI) layer over the substrate region. The method and system further includes etching a plurality of device structures in the EPI layer and providing a slot in the semiconductor substrate that is in contact with the buried layer and the substrate region. The method and system finally includes oxidizing the slot except at the bottom of the slot and providing metal within the slot.